

MAGNETO-RESISTIVE MEMORY CELL STRUCTURES WITH IMPROVED SELECTIVITY

Abstract of the Disclosure

A magneto-resistive memory comprising magneto-resistive memory cells is disclosed, comprising two pinned magnetic layers on one side of a free magnetic layer. The pinned magnetic layers are formed with anti-parallel magnetization orientations such that a net magnetic moment of the two layers is substantially zero. The influence of pinned magnetic layers on free magnetic layer magnetization orientations is substantially eliminated, allowing for increased predictability in switching behavior and increased write selectivity of memory cells.

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